


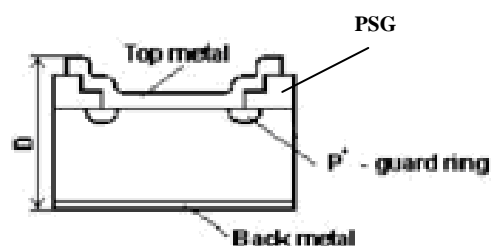
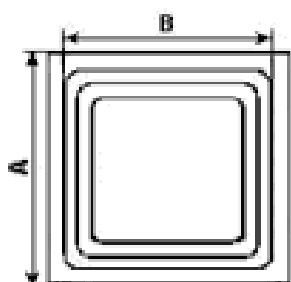
SCHOTTKY DIODES. KDS- 01040B

PRELIMINARY



July.2013

 VSP-MIKRON	1A/40V. Die Size-32mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_B	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ 25°C, $I_F=1,0A$	V_F	V	0,47	0,45
Maximum Reverse Current @ 25°C, $V_R=45V$ @ 25°C, $V_R=40V$ @ 100°C, $V_R=40V$	I_R	MA	- 0,30 15,0	0,30 0,20 10,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	20	-
Peak Repetitive Reverse Surge Current $J<150^\circ C$.	I_{RRM}	A	1,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV		
Voltage Rate of Change	dV/dt	V/ μS	10.000	
Operating Junction Temperature	T_J	°C	125	



DIM	ITEM	
Ax Ay	Die Size	810 810
Bx By	Top Metal Size	670 670
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.